

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/525,297
	Filing Date	02/15/2005
	Inventor(s)	James S. Im
	Art Unit	2822
	Examiner Name	Bac H. Au
	Attorney Docket Number	070050.2717

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	41.	6495405	12/17/2002	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
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	46.	20030013278	1/16/2003	Jang, Jin ; Kim, Kyung, Ho
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	56.	6573163	6/3/2003	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
	57.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti
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	60.	20030148565	8/7/2003	Yamanaka, Hideo
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	64.	6660575	12/9/2003	Zhang, Hongyong
	65.	6667198	12/23/2003	Shimoto, Shigeyuki ; Uchikoga, Shuichi
	66.	6693258	2/17/2004	Sugano, Yukiyasu ; Fujino, Masahiro ; Mano, Michio ; Asano, Akihiko ; Ino, Masumitsu ; Urazono, Takenobu ; Takatoku, Makoto
	67.	6734635	5/11/2004	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio
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	73.	20040169176	9/2/2004	Peterson, Paul, E. ; Stasiak, James
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	78.	20050059265	3/17/2005	Im, James
	79.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
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	81.	20050142450	6/30/2005	Jung, Yun
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	83.	20050202654	9/15/2005	Im, James
	84.	6961117	11/1/2005	Im, James S.
	85.	20060030164	2/9/2006	Im, James
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	91.	20070007242	1/11/2007	Im, James
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	97.	20070111349	5/17/2007	Im, James
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	Inventor(s)	James S. Im
	Art Unit	2822
	Examiner Name	Bac H. Au
	Attorney Docket Number	070050.2717

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